/ Descriptions

Silicon NPN transistor in a TO-126F Plastic Package.

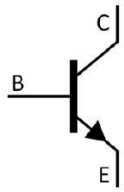
/ Features

4W output in complementary pair with 2SA886.

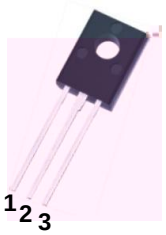
/ Applications

Medium power amplifier.

/ Equivalent Circuit



/ Pinning



PIN1 Emitter PIN 2 Collector PIN 3 Base

/ h_{FE} Classifications & Marking

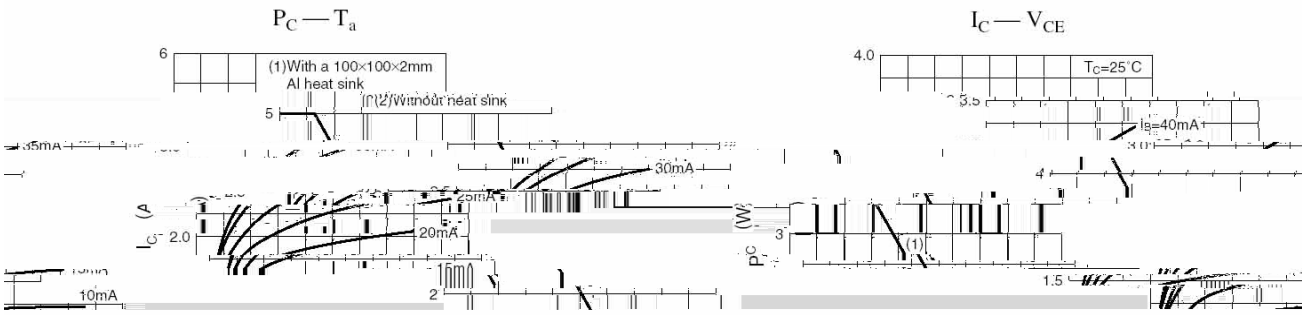
h_{FE} Classifications Symbol	P	Q	R
h_{FE} Range	50 100	80 160	120 220

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	50	V
Collector to Emitter Voltage	V_{CEO}	40	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	1.5	A
Collector Current – Continuous(Pulse)	I_{CP}	3.0	A
Collector Power Dissipation	P_C	1.2	W
Collector Power Dissipation*	*P_C(Tc=25)	5.0*	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

*With a 100×100×20mm AL heat sink

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=1.0mA I_E=0	50			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=2.0mA I_B=0	40			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=20V I_E=0			1.0	A
Collector Cut-Off Current	I_{CEO}	V_{CE}=10V I_B=0			100	A
Emitter Cut-Off Current	I_{EBO}	V_{EB}=5.0V I_C=0			10	A
	FE V	CE=5.0V I C= * 5	1	.	0	A
Vo	* CE(sat) I	C= V 2 B= * . 0	0 1 . 0		A 2 V	A
	T V	CE=5.0V I C=	0	.	5	A
		CB=20V E=0 f = 1 . 0 M H z				

/ Electrical Characteristic Curve



2SC1847

/ Marking Instructions

